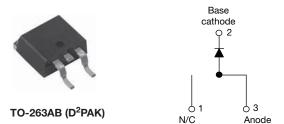


VS-8TQ080SPbF, VS-8TQ100SPbF

Vishay Semiconductors

High Performance Schottky Rectifier, 8 A

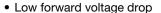
Anode



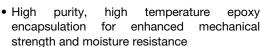
PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK)						
I _{F(AV)}	8 A						
V _R	80 V, 100 V						
V _F at I _F	0.72 V						
I _{RM} max.	7 mA at 125 °C						
T _J max.	175 °C						
Diode variation	Single die						
E _{AS}	7.5 mJ						

FEATURES











- · Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

The VS-8TQ... Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL CHARACTERISTICS VALUES									
I _{F(AV)}	Rectangular waveform	8	А						
V_{RRM}	Range	80, 100	V						
I _{FSM}	t _p = 5 μs sine	850	Α						
V _F	8 A _{pk} , T _J = 125 °C	0.58	V						
T _J	Range	-55 to +175	°C						

VOLTAGE RATINGS									
PARAMETER	SYMBOL	VS-8TQ080SPbF	VS-8TQ100SPbF	UNITS					
Maximum DC reverse voltage	V_{R}	80	100	V					
Maximum working peak reverse voltage	V_{RWM}	00	100	v					

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST COND	VALUES	UNITS					
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T _C = 157 °C	8	А					
Maximum peak one cycle non-repetitive surge current	l	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	850	А				
See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	230					
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 0.50 A, L = 60 mH		7.50	mJ				
Repetitive avalanche current	I _{AR}	Current decaying linearly to zer Frequency limited by T _J maxim	0.50	Α					



VS-8TQ080SPbF, VS-8TQ100SPbF

Vishay Semiconductors

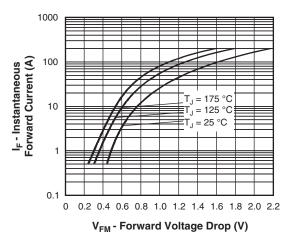
ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS				
		8 A	T _{.I} = 25 °C	0.72	V			
Maximum forward voltage drop	V _{FM} ⁽¹⁾	16 A	1j=25 C	0.88				
See fig. 1	V _{FM} (1)	8 A	T _{.1} = 125 °C	0.58				
		16 A	1J=125 C	0.69				
Maximum reverse leakage current	1 (1)	T _J = 25 °C	V _B = Rated V _B	0.55	mA			
See fig. 2	I _{RM} (1)	T _J = 125 °C	v _R = nateu v _R	7	IIIA 			
Maximum junction capacitance	C _T	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C		500	pF			
Typical series inductance	L _S	Measured lead to lead 5 n	8	nH				
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs				

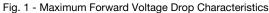
Note

 $^{^{(1)}\,}$ Pulse width < 300 $\mu s,$ duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T _J , T _{Stg}		-55 to +175	°C			
Maximum thermal resistance, junction to case		R _{thJC}	DC operation See fig. 4	2.0	°C/W			
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.50	C/VV			
Approximate weight				2	g			
Approximate weight				0.07	OZ.			
Mayorting toway	minimum			6 (5)	kgf ⋅ cm			
Mounting torque	maximum			12 (10)	(lbf · in)			
Marking device			Case style D ² PAK	8TQ	080S			
			Case style D-PAN	8TQ	100S			

Vishay Semiconductors





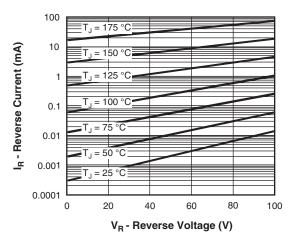


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

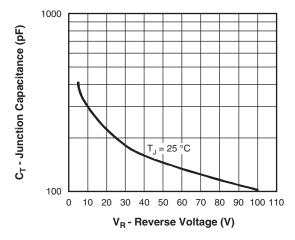


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

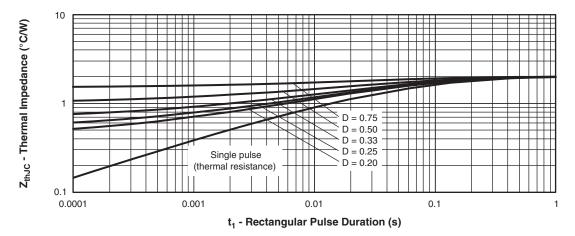


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

www.vishay.com

Vishay Semiconductors

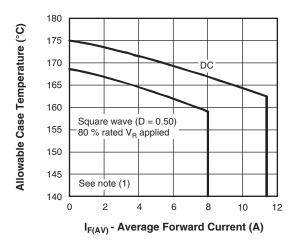


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

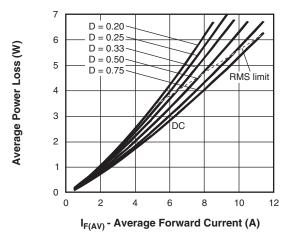


Fig. 6 - Forward Power Loss Characteristics

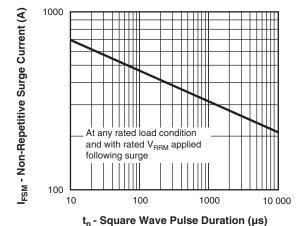


Fig. 7 - Maximum Non-Repetitive Surge Current

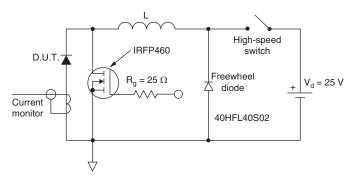


Fig. 8 - Unclamped Inductive Test Circuit

Note

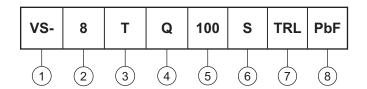
 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = 80 % rated V_R

VS-8TQ080SPbF, VS-8TQ100SPbF

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Current rating (8 A)

3 - Circuit configuration: T = TO-220

4 - Schottky "Q" series

080 = 80 V 100 = 100 V

6 - S = D²PAK

7 - • None = tube (50 pieces)

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

8 - PbF = lead (Pb)-free

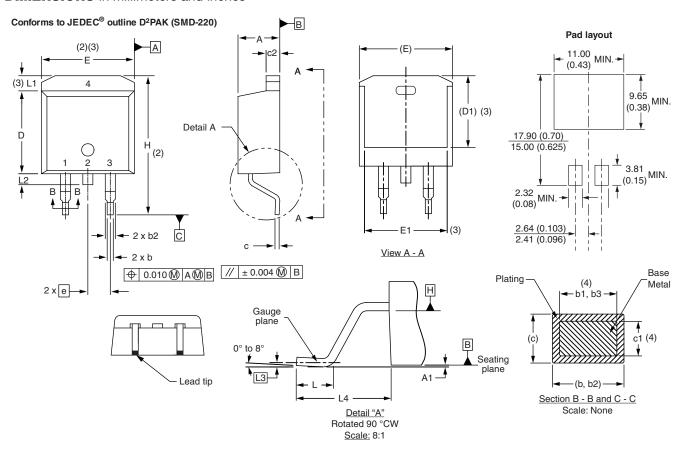
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					
SPICE models	www.vishay.com/doc?95291					



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000